

FDC365P

P-Channel Power Trench[®] MOSFET, -35V, -4.3A, 55mΩ

Product Overview

For complete documentation, see the data sheet.

This P-Channel MOSFET has been produced using a proprietary PowerTrench[®] technology to deliver low $r_{DS(on)}$ and optimized BV_{dss} capability to offer superior performance benefit in the applications.

Features

- Max $r_{DS(on)}$ = 55mΩ at $V_{GS} = 10V$, $I_D = -4.2A$
- Max $r_{DS(on)}$ = 80mΩ at $V_{GS} = -4.5V$, $I_D = -3.2A$
- RoHS compliant

Applications

- This product is general usage and suitable for many different applications.